

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	7	(opening with conductive) and ("dual gate" with CMOS) and ((Ntype n-type "n type" Ptype p-type "p type") with ("polycrystalline silicon" poly-silicon "poly silicon"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/12 16:30
L2	24	("dual gate" with CMOS) same SOI	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/12 16:32
L3	33	((partial partially) adj oxide) and SOI	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/12 16:35
L4	465	(partial partially) adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/12 16:51